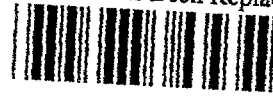


[Abstract of the Disclosure]

A process for manufacturing a semiconductor integrated circuit device is disclosed, including the steps of:

- 5 (a) coating a semiconductor substrate with a first conductive film, a first insulating film and a second insulating film sequentially in the order of recited lower layers and patterning the same to form a plurality of first conductive film patterns;
- 10 (b) forming a third insulating film over the semiconductor substrate after the step (a), on the side walls of the first conductive film patterns and over the second insulating film, and forming a fourth insulating film over the third insulating film;
- 15 (c) after the step (b), forming a mask with a first opening between the adjoining ones of the plurality of first conductive film patterns over the fourth insulating film, and etching the fourth insulating film, as exposed from the first opening of the mask,
- 20 under such a condition that the fourth insulating film is more easily etched off than the third and second insulating films, to form a second opening in the fourth insulating film; and
- (d) after the step (c), anisotropically etching the
- 25 third insulating film, as exposed from the second

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opening of the fourth insulating film, under such a
condition that the third insulating film is more
easily etched off than the first insulating film and
the fourth insulating film, to form a third opening
5 for exposing the upper face of the semiconductor
substrate, in the third insulating film between the
adjoining first conductive film patterns.